

isc Silicon NPN Darlington Power Transistor

2SD1983

DESCRIPTION

- · High DC Current Gain
- : h_{FE}= 4000(Min) @I_C= 1A
- · Low Collector Saturation Voltgae-
- : $V_{CE(sat)}$ = 1.5V(Max.)@ I_C= 1A
- Incorporating a built-in zener diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

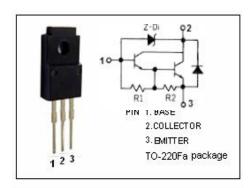


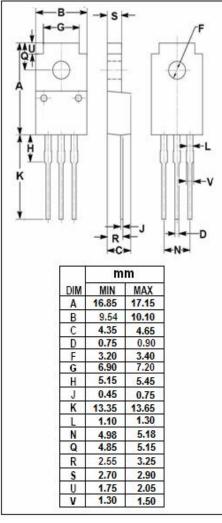
APPLICATIONS

· For low-frequency amplification

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage 50-70		V	
V _{CEO}	Collector-Emitter Voltage	50-70	V	
V _{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	1.5	Α	
I _{CP}	Collector Current-Peak	2.5	Α	
P _C	Collector Power Dissipation @ T _a =25℃	2	10/	
	Collector Power Dissipation @ T _C =25°C	20	W	
TJ	Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature Range	age Temperature Range -55~150		







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA; I _B = 0	50		70	V		
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C =0.1mA; I _E = 0	50		70	V		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1A; I _B = 1mA			1.5	V		
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1A; I _B = 1mA			2.2	V		
I _{CBO}	Collector Cutoff Current	V _{CB} = 50V; I _E = 0			10	μ Α		
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			3.0	mA		
h _{FE}	DC Current Gain	I _C = 1A; V _{CE} = 2V	4000		40000			
f⊤	Current-Gain—Bandwidth Product	I _C = 10mA; V _{CE} = 10V	100			MHz		

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